

Silicon NPN Power Transistors

2SC4793

DESCRIPTION

- With TO-220F package
- Complement to type 2SA1837
- High transition frequency

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

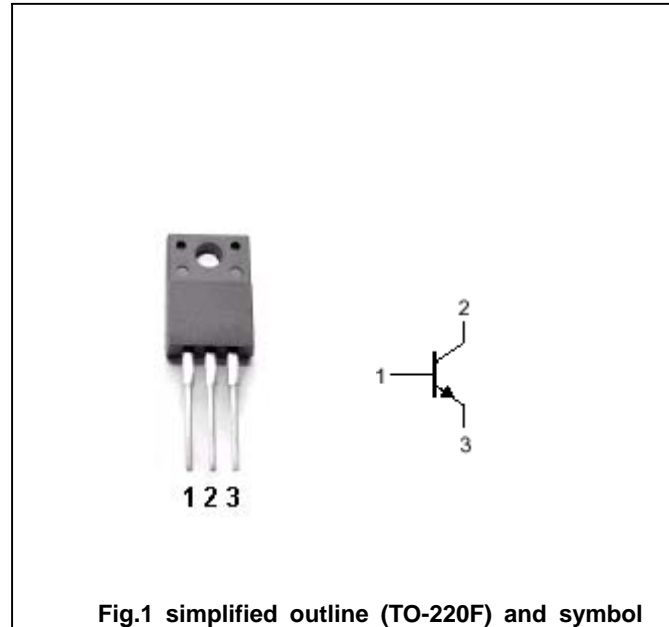


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|---------------------------|--------------------|---------|------|
| V _{CB0} | Collector-base voltage | Open emitter | 230 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 230 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I _c | Collector current | | 1 | A |
| I _B | Base current | | 0.1 | A |
| P _C | Collector dissipation | T _C =25 | 20 | W |
| P _C | Collector dissipation | T _a =25 | 2.0 | W |
| T _j | Junction temperature | | 150 | |
| T _{stg} | Storage temperature | | -55~150 | |

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CHARACTERISTICS

T_j=25 unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|--------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CEO} | Collector-emitter breakdown voltage | I _C =10mA ; I _B =0 | 230 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =0.5A I _B =50mA | | | 1.5 | V |
| V _{BE} | Base-emitter voltage | I _C =0.5A ; V _{CE} =5V | | | 1.0 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =230V I _E =0 | | | 1.0 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V; I _C =0 | | | 1.0 | μ A |
| h _{FE} | DC current gain | I _C =0.1A ; V _{CE} =5V | 100 | | 320 | |
| C _{OB} | Output capacitance | I _E =0; V _{CB} =10V;f=1MHz | | 20 | | pF |
| f _T | Transition frequency | I _C =0.1A ; V _{CE} =10V | | 100 | | MHz |

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PACKAGE OUTLINE

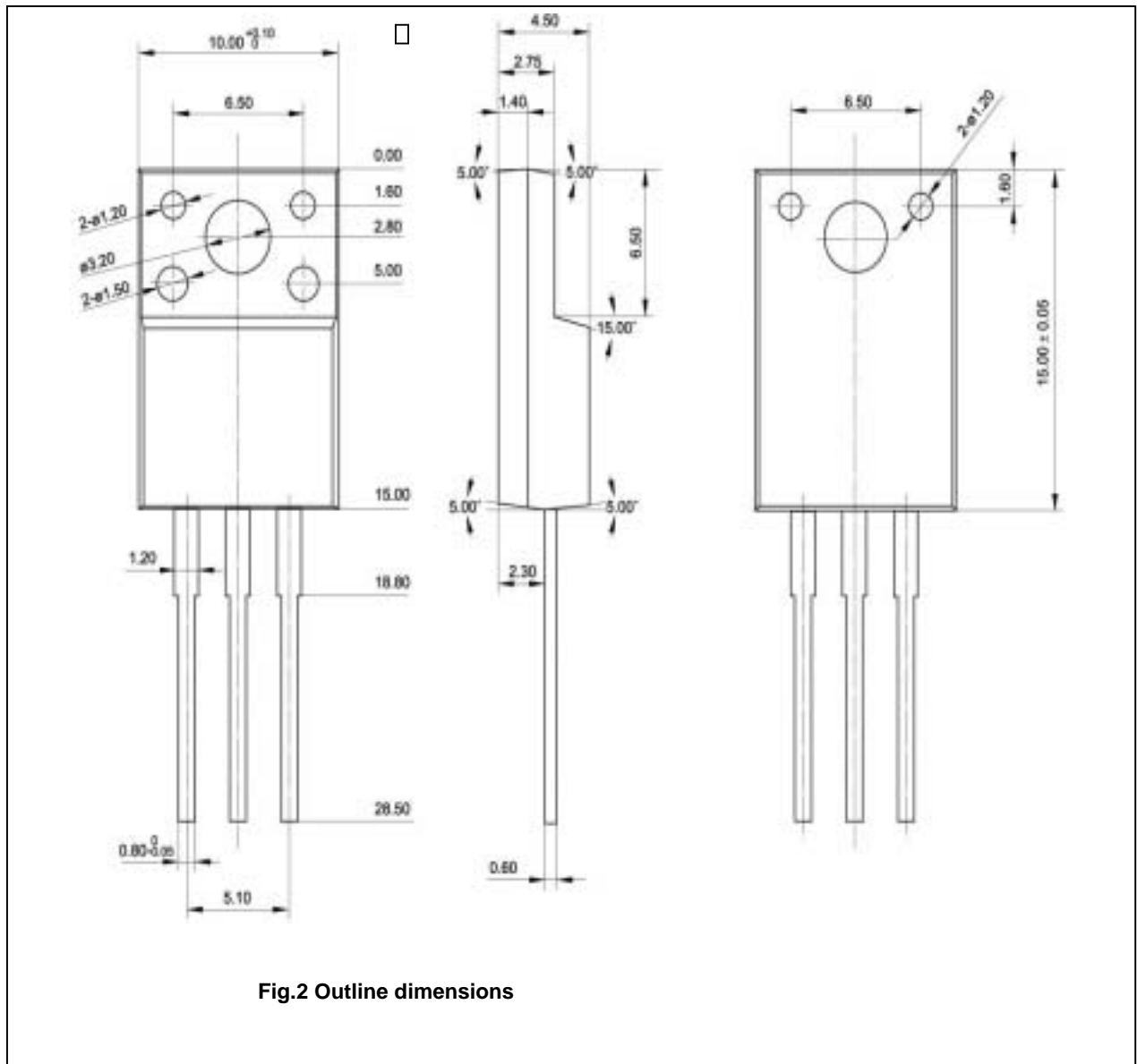


Fig.2 Outline dimensions